Thereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA.22313, on July 23, 2004. The applicant and/or attorney makes the date of deposit as the filing date. Depositor: Teri McDonald

[Security 1.2.]

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of ____:

Kangguo Cheng, et al.

July 23, 2004

Group Art Unit: Unassigned

Serial No. 10/710,608

Examiner: Unassigned

Filed: 12/31/2001

International Business Machines Corporation

2070 Route 52

Hopewell Junction, NY 12533

TITLE: PATTERNED STRAINED SEMICONDUCTOR SUBSTRATE AND DEVICE

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the non-US patents and publications as listed on Form PTO-1449, attached hereto.

In citing these documents, no representation is made nor intended as to the pertinency or nonpertinency of the art, that better art than that listed is not available, or that other art is not applicable.

If any fees are required, the Commissioner is hereby authorized to charge such fees to Deposit Account No. 09-0458.

Respectfully submitted, Kanggou Cheng, et al.

Joseph P. Abate, Attorney Registration No. 30,238

Telephone No.)845-894-4633

49 (Modified) ATTY. DOCKET NO. SERIAL NO. FIS920040150US1 10/710,608 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT: APPLICANT'S INFORMATION DISCLOSURE Kangguo CHENG, et al. **STATEMENT** GROUP: (Use several sheets if necessary) FILING DATE:

07/23/2004 Unassigned REFERENCE DESIGNATION U.S. PATENT DOCUMENTS **EXAMINER DOCUMENT FILING DATE INITIALS NUMBER** DATE **NAME CLASS SUBCLASS** (IF APPRO.) 6,228,694 B1 5/8/2001 Doyle et al. 6,406,973 B1 6/18/2002 Lee 6,281,532 B1 8/28/2001 Doyle et al. 5,683,934 11/4/97 Candelaria 6,368,931 B1 4/9/2002 Kuhn, et al. 5,310,446 5/10/94 Konishi et al. 4,853,076 8/1/89 Tsaur et al. US 2002/0090791 A1 7/11/2002 Doyle et al. US 2002/0074598 A1 6/20/2002 Doyle et al. 6,509,618 B2 7/21/2003 Jan et al. 6,476,462 B2 Shimizu et al. 11/5/2002 6,362,082 B1 3/26/2002 Doyle et al. 5/8/2001 6,228,694 B1 Doyle et al. 10/15/96 Asakawa et al. 5,565,697 US 2003/0040158 A1 2/27/2003 Saitoh US 2002/0086472 A1 7/4/2002 Roberds et al. 6,521,964 B1 2/18/2003 Jan et al. 6,506,652 01/14/03 Jan et al. FOREIGN PATENT DOCUMENTS DOCUMENT TRANSLATION NUMBER DATE **COUNTRY** CLASS SUBCLASS YES NO OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.) EXAMINER DATE CONSIDERED

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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